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PATENT # 8/0
Attorney Docket No.: SAM-0219

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jae-Phil Boo, et al.

Serial No.: 09/902,243

Filing Date: July 10, 2001

Title: METHOD OF FABRICATING A NON-VOLATILE MEMORY DEVICE
HAVING A TUNNEL-INSULATING LAYER INCLUDING MORE THAN
TWO PORTIONS OF DIFFERENT THICKNESS

Examiner: Pham, L.

Group Art Unit: 2814

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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2-28-03

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Amy Green
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Assistant Commissioner for Patents

Washington, DC 20231

enter memo 4/11/03
AMENDMENT AFTER FINAL

Sir:

The following is in response to the Office Action dated November 29, 2002. Please amend the application as follows.

In the claims:

Please cancel claim 2.

Please replace claims 1, 3, 7 and 9 with the following rewritten claims.

1. (Twice Amended) A method of fabricating a non-volatile memory device having a tunnel insulating layer, comprising:

sequentially depositing said tunnel insulating layer, a floating gate conductive layer, and a first insulating layer over a semiconductor substrate, said tunnel insulating layer including at least two portions of different thicknesses, and said conductive layer serving as a floating gate in a